FOWLP Thermal Debonding: Easing Manufacturing Constraints

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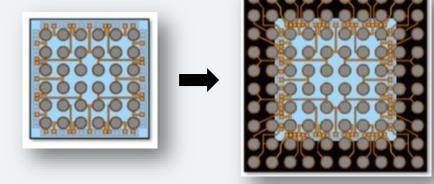




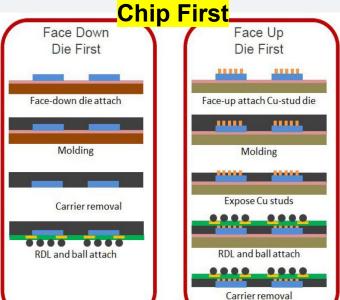
What is Fanout?

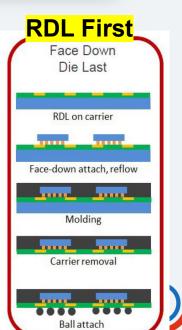


- Fan-out is a type of advanced chip packaging where the redistribution layer (RDL) are routed outside the surface area of the die.
- Several noted advantages are:
 - Good electrical performance
 - Enables high density routing
 - Enables multi die package configuration



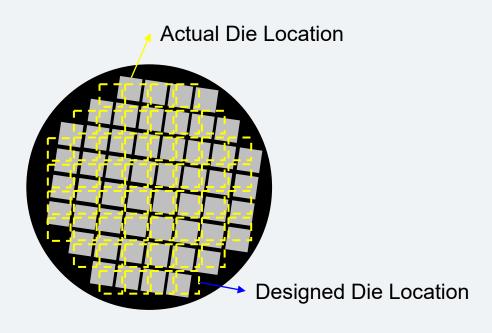
Credits: ASE





Fanout's Dilemma





Die Shift is a defect in which the actual die location has an offset from the pre-defined position by a certain distance.



Warpage is the physical deformation encountered by the wafer due to coefficient of thermal expansion (CTE) mismatch between silicon and mold



Fanout Process



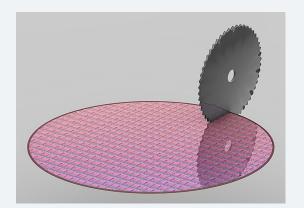
Chip First – Face up or Face down

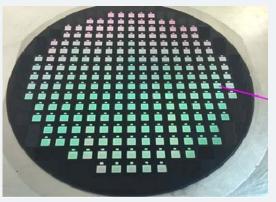
Die Preparation

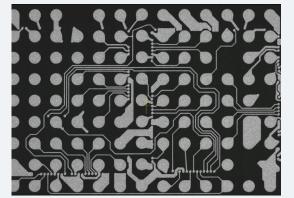
Wafer Reconstruction

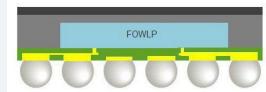
Layer Build Up (Redistribution)

Die/Package Finishing









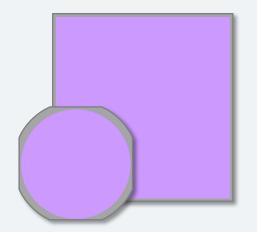
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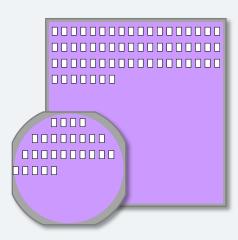
Fanout Reconstruction Process



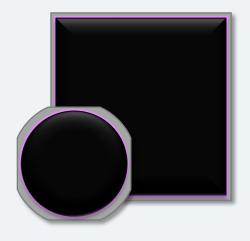
Carrier Lamination



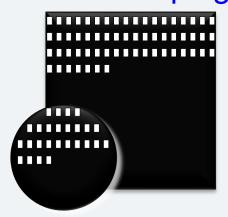
Die Bonding



Molding



Carrier Removal and Detaping



The reconstruction (wafer) or panelization (panel) process is the key differentiator of Fanout in comparison to *WLCSP/Fan-in process



Thermal Debond



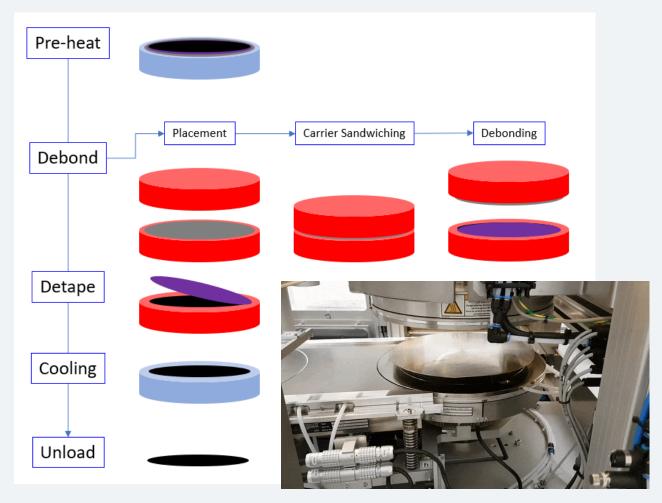
Thermal debonding is the process of separating the reconstructed wafer from its carrier.

The whole process is composed of several thermal treatment with the aim of

- Stress free carrier removal
- Smooth Detaping
- No tape residue
- Minimal warpage

Key parameters

- Temperature
- Soak time
- Detape speed
- Detape angle





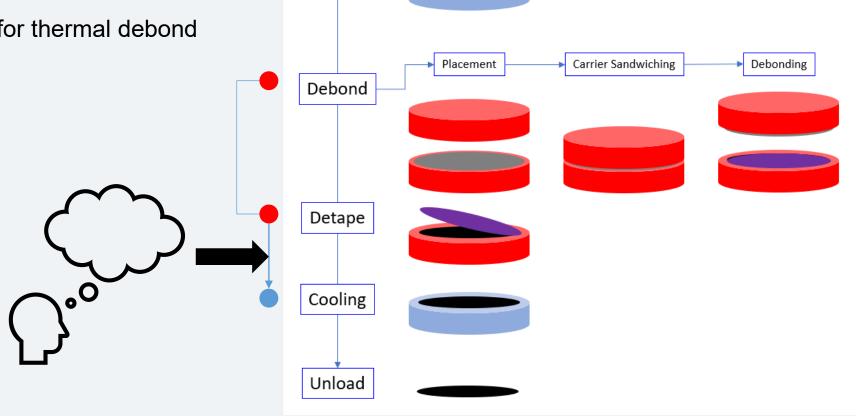
Pre-heat

Thermal Debond



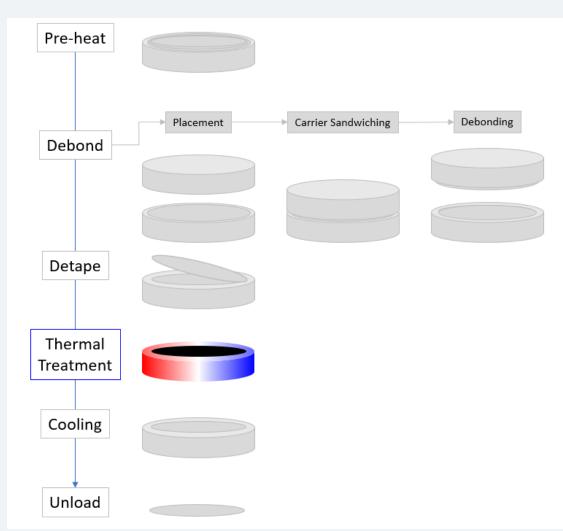
The wafer then goes into cooling stage.

This base process for thermal debond









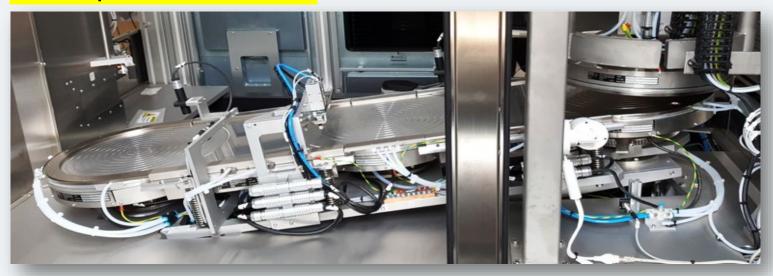
Improvement for thermal Debond

1. Add a second heating treatment





TriTemp and AirCushion





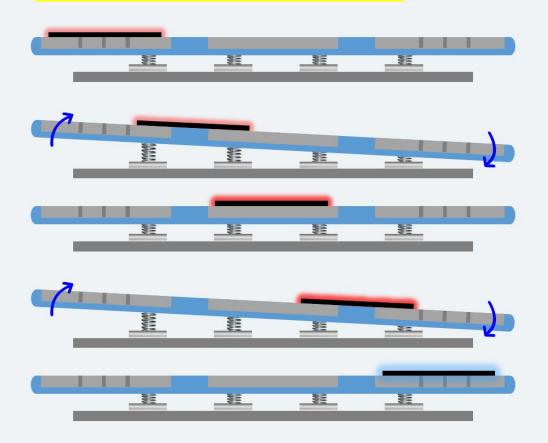
Benefits of a 2nd heating treatment

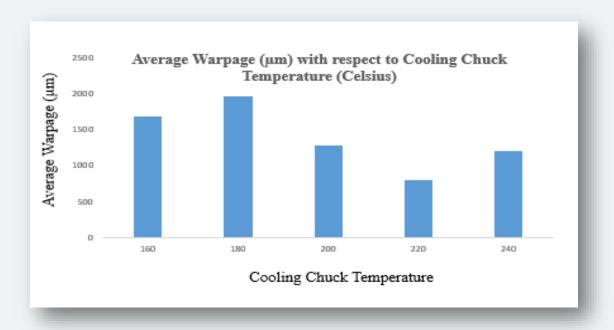
- 1. Allows "shock and lock" method which is a way to lock flatness into the wafer
- 2. Intermediate slow cooling; instead of straight from debond temp (~180°C to 200°C) to room temperature, an intermediate temp of ~60°C to 110°C is done





Shock and Lock



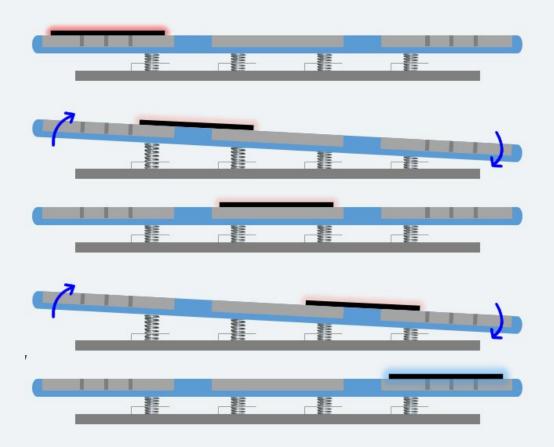


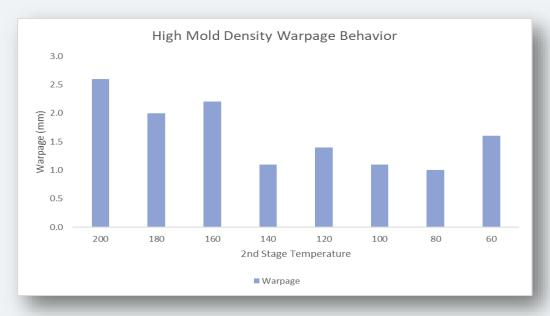
*For wafers with higher silicon content, high temperature for 2nd treatment showed better warpage performance





Intermediate - Slow Cooling

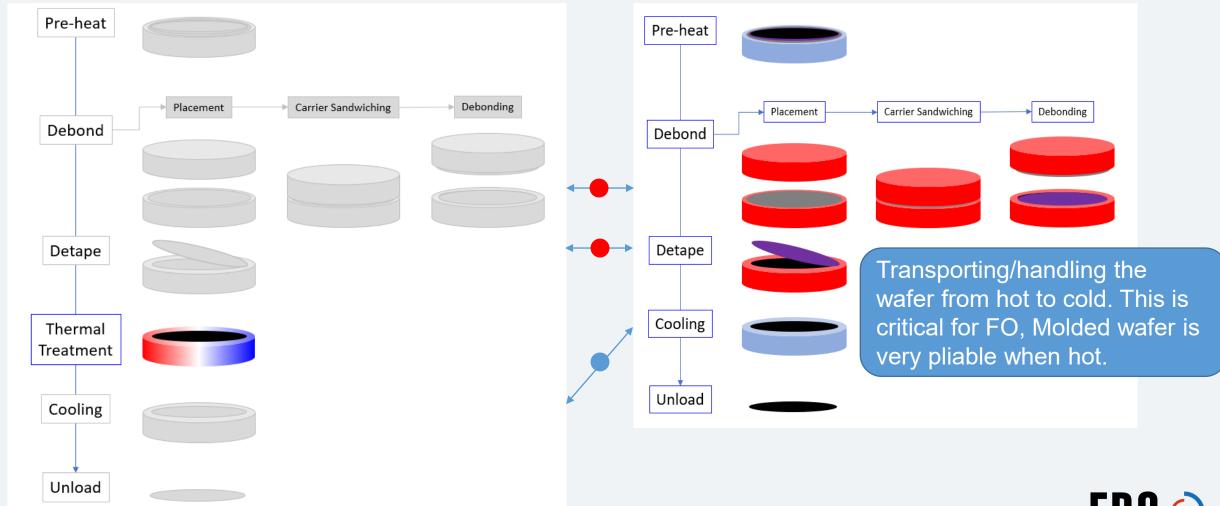




For wafers with more mold compound (thick overmold), warpage is minimal with slow cooling

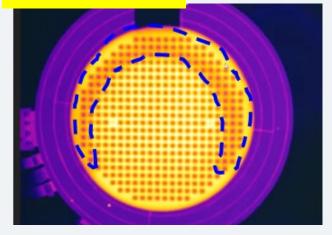




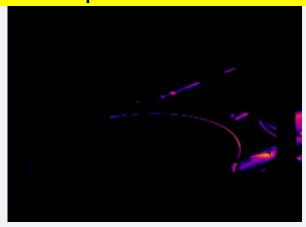


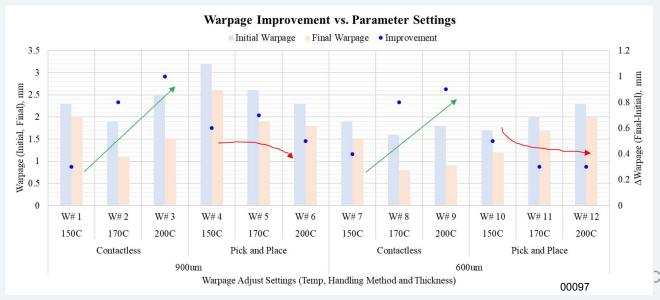


Pick and Place



TriTemp and AirCushion





- We have observed a different heat dissipation behavior between slide system and pick and place
- Slide system being more uniform and resulting to better warpage behavior
- Data also shows increasing temp result to higher warpage when doing pick and place



Confidential

Conclusion



- Enhancing Thermal Debond method shows great benefits in reducing warpage, this is done by
 - Adding a 2nd stage of thermal treatment
 - Eliminating pick and place handling when wafer is in high temperature state
- This minimal warpage output of the end process of the reconstruction module can greatly address the issues of handling in the next FO step which in RDL



Thank You! Vielen Dank!

in ERS electronic GmbH



